

Indian Institute of Technology Patna Bihta, Patna – 801106, India DEPARTMENT OF PHYSICS

MID-SEMESTER EXAMINATION DATE: 25-09-2019

	te: 2hours URSE NO: PH401 COURSE TITLE: Introduction to No. 11	30
	URSE NO: PH401 COURSE TITLE: Introduction to Nanomaterials Attempt all (Note: No explanation during the examination)	Questions
1	1. Why not engineering possible beyond 10 ⁻¹⁰ m in length scale?	
2	2. Does molecular machine exist today? If yes, give an example. If not, Why?	[2
3	3. What was the gist of Feynman lecture "Thora's about of	[2
4	What was the gist of Feynman lecture "There's plenty of room at the bottom" at Caltech on 1959? [2]	
1	Write degrees of confinement and degrees of freedom for bulk, quantum well, nanowire and quantum dot.	
5	Lenses are to be antireflected for ultraviolet electromagnetic radiation of wavelength 2	[2]
	$n_i = 1.40$ is available with an engineer. What will be the thickness of quoting on the index $n_{ij} = 1.48$ to protect LIV light of small and $n_{ij} = 1.48$ to protect LIV light of small $n_{ij} = 1.48$	00nm. MgF ₂ with
	index $n_{lense}=1.48$ to protect UV-light of wavelength 200nm?	lens of refractive
	Or	
	Write a short note on top down method.	
6.		[3]
	Or	
	Why is the electron lithography required for nanotechnology? What will be the reso-	r ar ar v
	lithography by using an electron of wavelength (λ ~)2nm? Consider the best arrangement of the	
	nanography secup. Use the instrumental constant () 6 and refractive index 1.5	2000
7.	Write a short note on ball mill method to produce nanomaterials. What is the ultimachieved in this method?	[3]
	achieved in this method?	nate size can be
	Or	
	Write a short note on pulse laser deposition.	(2)
8.	What is/are the difference/s between multicolours in butterfly mornho polarides to	[3]
	P, John M. Grow at Diffusi museum, London' What are the reasons for he	th
	these endses used for modern technological development? Give two example	e of commonsial
	products from each category.	F 2.3
9.	the selficonductor: Find our the continement length for CdC	[4] Semiconductor
	The effective masses of note and electron are $m_e \approx 0.2 m_e$ and $m_e \approx 0.7 m_e$ in the	r mant
	electron are in the order of 10 m/s. Sketch the difference of 10 m/s.	ant soul
	renging for the above semiconductor. [Rest mass of the electron = 9.1x10 ⁻³¹ kg and plant?	s constant 6.63
	10 111 18/5]	6.43
10.	What is the magic number for the nanoparticles? Derive the expression to obtain the ma	[4]
	structure. Sketch the surface to volume atom ratio versus particle size for this struc	fure and diameter
	its importance for nanoscience.	
	REST OF LUCK	[5]